



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate Transistors

KTC4076 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 100 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 500 mA

Collector-base voltage

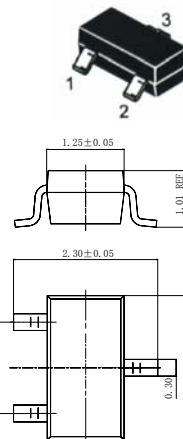
$V_{(BR)CBO}$: 35 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-323

1. BASE
2. EMITTER
3. COLLECTOR



Unit: mm

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	35			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=35V, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1V, I_C=100mA$	70		240	
	$h_{FE(2)}$	$V_{CE}=6V, I_C=400mA$ O Y	25 40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$			0.25	V
Base-emitter voltage	V_{BE}	$V_{CE}=1V, I_C=100mA$			1	V
Transition frequency	f_T	$V_{CE}=6V, I_C=20mA$		300		MHz
Collector output capacitance	C_{ob}	$V_{CB}=6V, I_E=0, f=1MHz$		7		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	70-140	120-240
Marking	WO	WY